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making a nitrogen concentration of part of the gate insulating film except under the gate electrodes lower than a nitrogen concentration of part of the gate insulating film which lies under the gate electrodes by oxidizing the gate electrodes and the gate insulating film by at least one of a vaporizer method, an oxyhydrogen combustion method, and a wet oxidation method performed at temperatures not lower than 950°C; and

forming impurity diffused layers on both sides of the respective gate electrodes in the semiconductor substrate.

REMARKS

Favorable reconsideration of this application as presently amended and in light of the following discussion is respectfully requested.

Claims 1-4, 7, 10, 12-18, 20 and 22 are pending in the present application. Claim 10 has been amended by the present amendment.

Claim 10 has been amended to include a feature which was inadvertently not included in the previous response. This additional feature is the same feature included in other independent claims such as Claims 1 and 12, for example. It is believed no new matter has been added.

Consequently, an action on the merits is earnestly solicited.

Respectfully submitted,

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IN THE CLAIMS

10. (Twice Amended) A semiconductor device manufacturing method comprising:

forming a gate insulating film in an oxynitride form on a main surface of a semiconductor substrate;

forming gate electrodes on the gate insulating film;

making a nitrogen concentration of part of the gate insulating film except under the gate electrodes lower than a nitrogen concentration of part of the gate insulating film which lies under the gate electrodes by oxidizing the gate electrodes and the gate insulating film by at least one of a vaporizer method, an oxyhydrogen combustion method, and a wet oxidation method performed at temperatures not lower than 950°C; and

forming impurity diffused layers on both sides of the respective gate electrodes in the semiconductor substrate.

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